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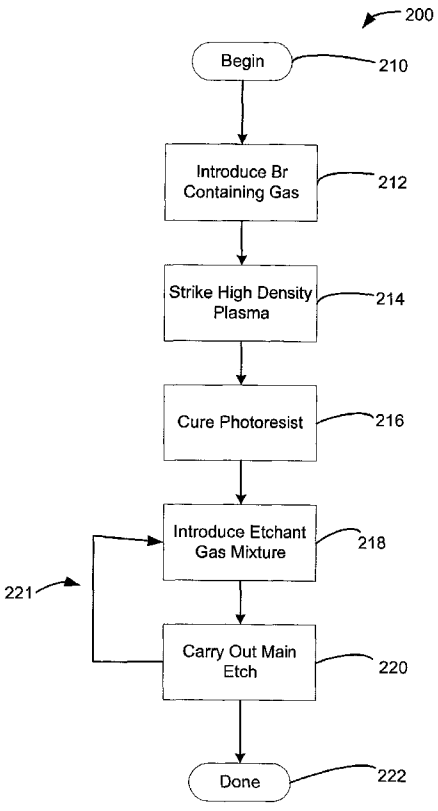
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[Continued on next page]

(54) Title: METHOD AND COMPOSITIONS FOR HARDENING PHOTORESIST IN ETCHING PROCESSES



(57) Abstract: A method for etching a wafer having a pattern of photoresist material thereon is disclosed. The method includes curing the photoresist material with a bromine containing plasma. Then a main etch of the wafer is carried out. A method for curing a pattern of photoresist material on a wafer is also disclosed. The curing method includes providing a bromine containing plasma and exposing the photoresist material to the plasma, such that a layer of the wafer below the photoresist material is not etched through. A composition of a plasma for curing a photoresist material on a wafer in a high density plasma processing device includes bromine.

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